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Sheet 1 of 2

FORM PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. FIS920030236US1	Application No. 10/605,906
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)		Applicant An L. STEEGEN et al.	
		Filing Date 11/05/2003	Group 2813

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EXAMINER	Stephen W. Smoot	DATE CONSIDERED	August 1, 2006
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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EXAMINER	Stephen W. Smoot			DATE CONSIDERED August 1, 2006			
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